

2SK3888-01MR

N-CHANNEL SILICON POWER MOSFET

Outline Drawings (mm) 200406

FUJI POWER MOSFET Super FAP-G Series

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

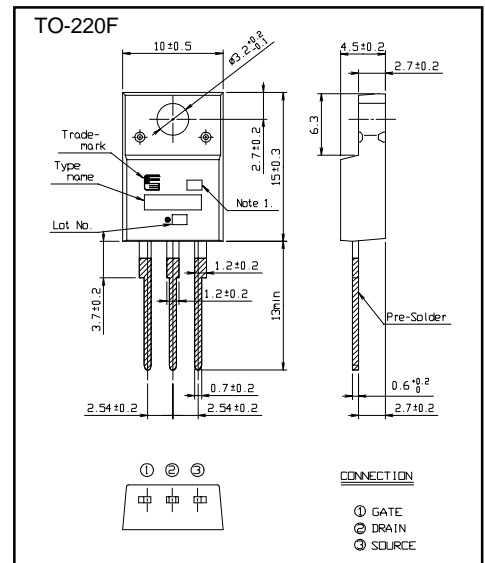
Applications

- Switching regulators
- DC-DC converters
- UPS (Uninterruptible Power Supply)

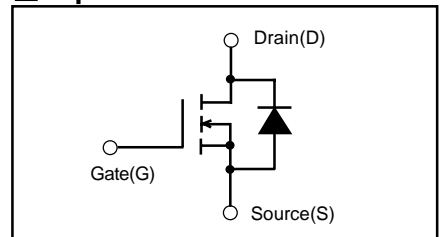
Maximum ratings and characteristic

Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V _{DS}	600	V	
	V _{DSX}	600	V	V _{GS} =-30V
Continuous Drain Current	I _D	9	A	
Pulsed Drain Current	I _{D(puls)}	±36	A	
Gate-Source Voltage	V _{GS}	±30	V	
Maximum Avalanche current	I _{AR}	9	A	Note *1
Non-Repetitive Maximum Avalanche Energy	E _{AS}	462.3	mJ	Note *2
Repetitive Maximum Avalanche Energy	E _{AR}	6.0	mJ	Note *3
Maximum Drain-Source dV/dt	dV _{DS} /dt	20	kV/μs	V _{DS} ≤600V
Peak Diode Recovery dV/dt	dV/dt	5	kV/μs	Note *4
Max. Power Dissipation	P _D	60	W	T _c =25°C
		2.16		T _a =25°C
Operating and Storage Temperature range	T _{ch}	+150	°C	
	T _{stg}	-55 to +150	°C	
Isolation Voltage	V _{ISO}	2	kVrms	t=60sec f=60Hz



Equivalent circuit schematic



Note *1: T_{ch} ≤ 150°C, Repetitive and Non-repetitive
 Note *2: Starting T_{ch}=25°C, I_{AS}=3.6A, L=65.4mH, V_{CC}=60V, R_G=50Ω
 EAS limited by maximum channel temperature and avalanche current.
 See to the 'Avalanche Energy' graph
 Note *3: Repetitive rating: Pulse width limited by maximum channel temperature.
 See to the 'Transient Thermal impedance' graph
 Note *4: I_F ≤ -I_D, -di/dt=50A/μs, V_{CC} ≤ BV_{DSS}, T_{ch} ≤ 150°C

Electrical characteristics (Tc = 25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA V _{GS} =0V	600			V
Gate Threshold Voltage	V _{GS(th)}	I _D =250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =600V V _{GS} =0V			25	μA
		V _{DS} =480V V _{GS} =0V			250	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V V _{DS} =0V			100	nA
Drain-Source On-State Resistance	R _{DS(on)}	I _D =4.5A V _{GS} =10V		0.82	1.00	Ω
Forward Transconductance	g _{fs}	I _D =4.5A V _{DS} =25V	4.5	9.0		S
Input Capacitance	C _{iss}	V _{DS} =25V		950	1425	pF
Output Capacitance	C _{oss}	V _{GS} =0V		130	195	
Reverse Transfer Capacitance	C _{rss}	f=1MHz		6.0	9.0	
Turn-On Time t _{on}	td(on)	V _{CC} =300V I _D =4.5A		16	24	ns
	t _r	V _{GS} =10V		6.0	9.0	
Turn-Off Time t _{off}	td(off)	R _{GS} =10Ω		33	50	
	t _f			5.5	8.3	
Total Gate Charge	Q _G	V _{CC} =300V		25	38	nC
Gate-Source Charge	Q _{GS}	I _D =9A		10	15	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		8.0	12.0	
Diode forward on-voltage	V _{SD}	I _F =9A V _{GS} =0V T _{ch} =25°C		1.10	1.50	V
Reverse recovery time	t _{rr}	I _F =9A V _{GS} =0V		860		ns
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		7.0		μC

Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			2.083	°C/W
	R _{th(ch-a)}	channel to ambient			58	°C/W

Characteristics

